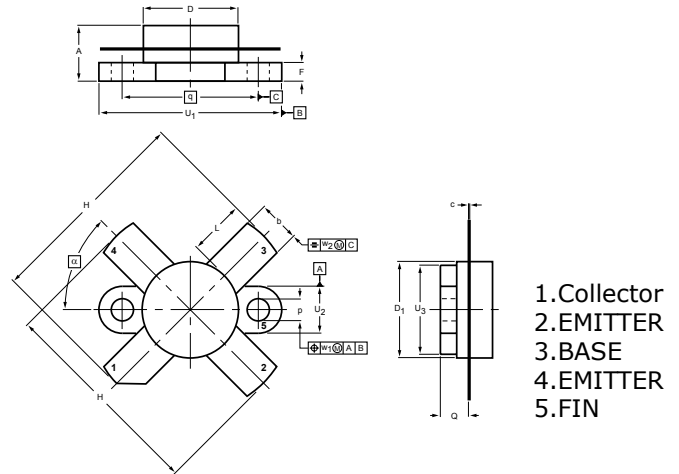


## DESCRIPTION

Designed For HF Band SSB  
LINEAR POWER AMPLIFIER

## FEATURES

- Specified 12.5V, 30MHz Characteristics
- $P_o = 100W$  PEP(Min.)
- $G_p = 13$  dB (Min) @30M
- Omnigold™ Metalization System



## DIMENSIONS

NOTE: ALL ELECTRODES ARE ISOLATED FROM FLANGE.

UNIT	A	b	c	D	D <sub>1</sub>	F	H	L	p	Q	q	U <sub>1</sub>	U <sub>2</sub>	U <sub>3</sub>	w <sub>1</sub>	w <sub>2</sub>	α
mm	7.27	5.82	0.16	12.86	12.83	2.67	28.45	7.93	3.30	4.45	18.42	24.90	6.48	12.32	0.51	1.02	45°
	6.17	5.56	0.10	12.59	12.57	2.41	25.52	6.32	3.05	3.91		24.63	6.22	12.06			
inches	0.286	0.229	0.006	0.506	0.505	0.105	1.120	0.312	0.130	0.175	0.725	0.98	0.255	0.485	0.02	0.04	
	0.243	0.219	0.004	0.496	0.495	0.095	1.005	0.249	0.120	0.154		0.97	0.245	0.475			

## MAXIMUM RATINGS

CHARACTERISTICS	SYMBOL	RATINGS	UNITS
Collector-Base Voltage	$V_{CB0}$	45	V
Collector-Emitter Voltage	$V_{CES}$	45	V
Collector-Emitter Voltage	$V_{CEO}$	20	V
Collector Current	$I_c$	25	A
Emitter-Base Voltage	$V_{EBO}$	4.5	V
Collector Power Dissipation	$P_{DISS}$	320	W
Junction Temperature	$T_J$	-65 to 175	°C
Storage Temperature Range	$T_{STG}$	-65 to 175	°C

## ELECTRICAL CHARACTERISTICS

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_c=50mA, I_B=0$	20	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CES}$	$I_c=200mA, V_{EB}=0$	45	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=10mA, I_c=0$	4.5	-	-	V
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = 30V, I_E = 0$	-	-	500	uA
DC Current Gain	$h_{FE}$	$V_{CE}=5V, I_c=10A$	10	50	-	
Power Gain	$G_p$	$V_{CC}=12.5V, P_{OUT}=100W, f=30MHz, P_{IN}=8 W$	13.0	14.0	-	dB
Collector Efficiency	$\eta_c$		40	-	-	%
Intermodulation Distortion	IMD		-	-30	-	dB
Collector Output Capacitance	$C_{ob}$	$V_{CB}=12.5V, I_E=0, f=1MHz$	-	-	700	pF

Note : Above parameters , ratings , limits and conditions are subject to change.